

1HN04CH



ON Semiconductor®

<http://onsemi.com>

Power MOSFET

100V, 8Ω, 270mA, Single N-Channel

Features

- 4V drive
- Halogen free compliance

Specifications

Absolute Maximum Ratings at $T_a = 25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	V_{DS}		100	V
Gate to Source Voltage	V_{GS}		± 20	V
Drain Current (DC)	I_D		270	mA
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	1080	mA
Power Dissipation	P_D	When mounted on ceramic substrate (900mm ² ×0.8mm)	0.6	W
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

This product is designed to “ESD immunity < 200V*”, so please take care when handling.

* Machine Model

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm ² ×0.8mm)	$R_{\theta JA}$	208	°C/W

Electrical Characteristics

 at $T_a = 25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}$, $V_{GS} = 0\text{V}$	100			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$			1	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16\text{V}$, $V_{DS} = 0\text{V}$			± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = 10\text{V}$, $I_D = 100\mu\text{A}$	1.2		2.6	V
Forward Transconductance	g_{FS}	$V_{DS} = 10\text{V}$, $I_D = 140\text{mA}$		260		mS
Static Drain to Source On-State Resistance	$R_{DS(on)1}$	$I_D = 140\text{mA}$, $V_{GS} = 10\text{V}$		6	8	Ω
	$R_{DS(on)2}$	$I_D = 70\text{mA}$, $V_{GS} = 4\text{V}$		6.8	9.8	Ω
Input Capacitance	C_{iss}	$V_{DS} = 20\text{V}$, $f = 1\text{MHz}$		15		pF
Output Capacitance	C_{oss}			3.1		pF
Reverse Transfer Capacitance	C_{rss}			0.9		pF

Continued on next page.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

1HN04CH

Continued from preceding page.

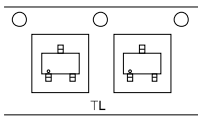
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		10		ns
Rise Time	t_r			7.4		ns
Turn-OFF Delay Time	$t_{d(off)}$			58		ns
Fall Time	t_f			39		ns
Total Gate Charge	Q_g	$V_{DS}=50V, V_{GS}=10V, I_D=270mA$		0.9		nC
Gate to Source Charge	Q_{gs}			0.19		nC
Gate to Drain "Miller" Charge	Q_{gd}			0.26		nC
Forward Diode Voltage	V_{SD}	$I_S=270mA, V_{GS}=0V$		0.88	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

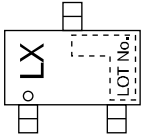
Ordering & Package Information

Device	Package	Shipping	note
1HN04CH-TL-W	CPH3, SC-59 SOT-23, TO-236	3,000 pcs. / reel	Pb-Free and Halogen Free

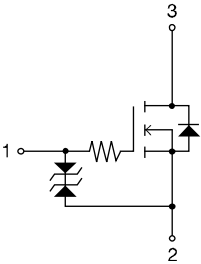
Packing Type:TL



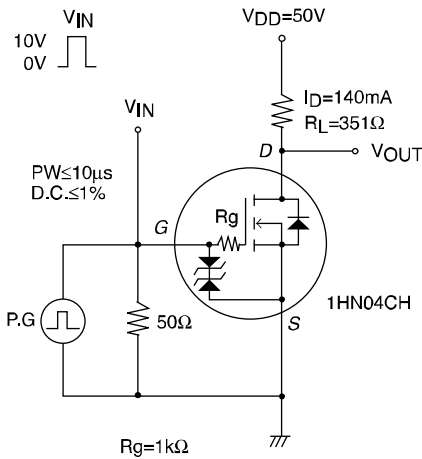
Marking

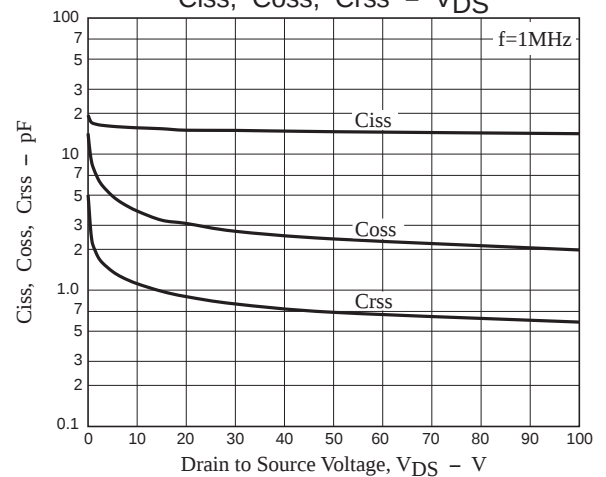
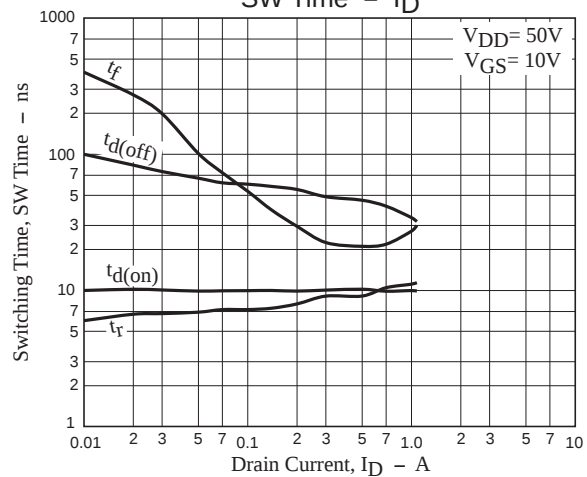
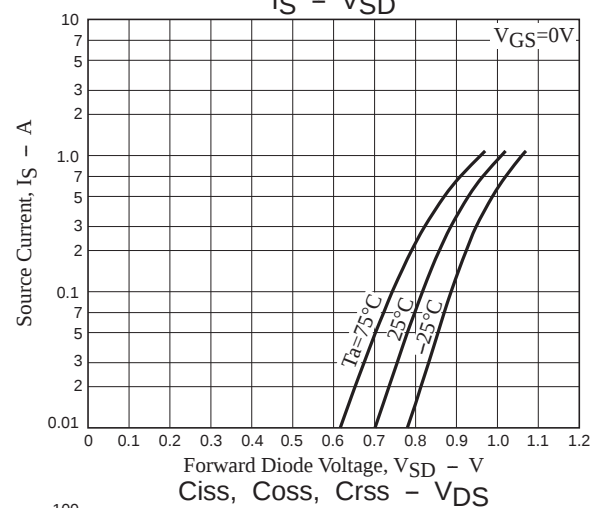
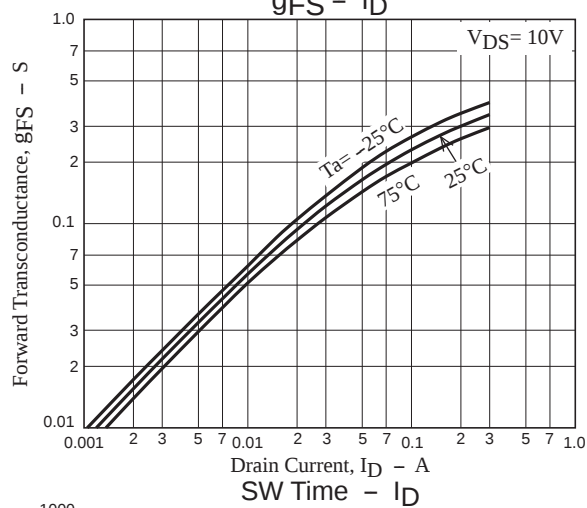
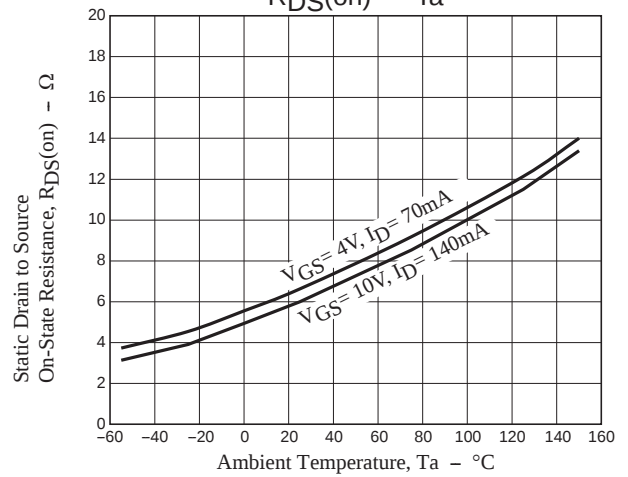
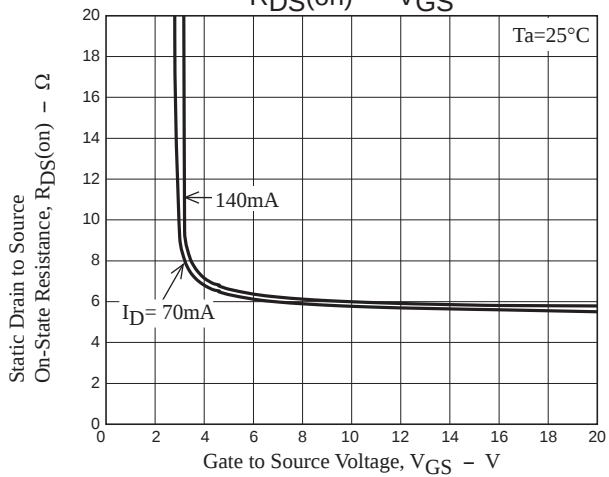
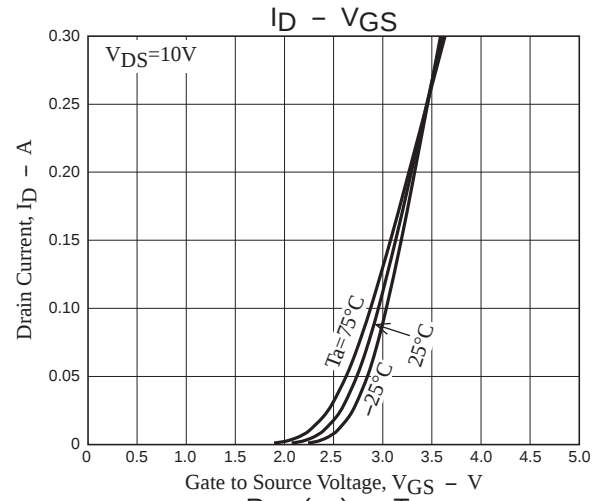
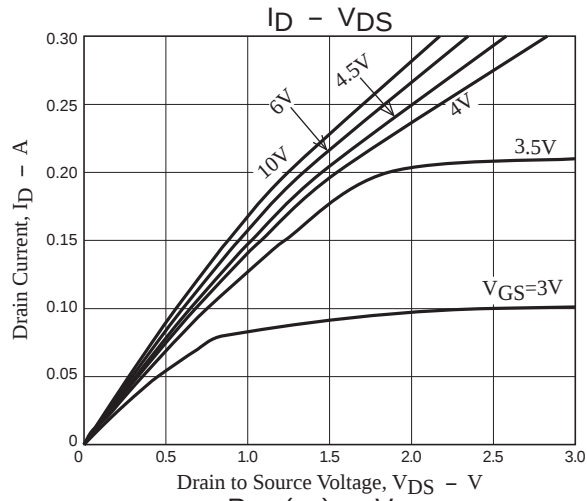


Electrical Connection

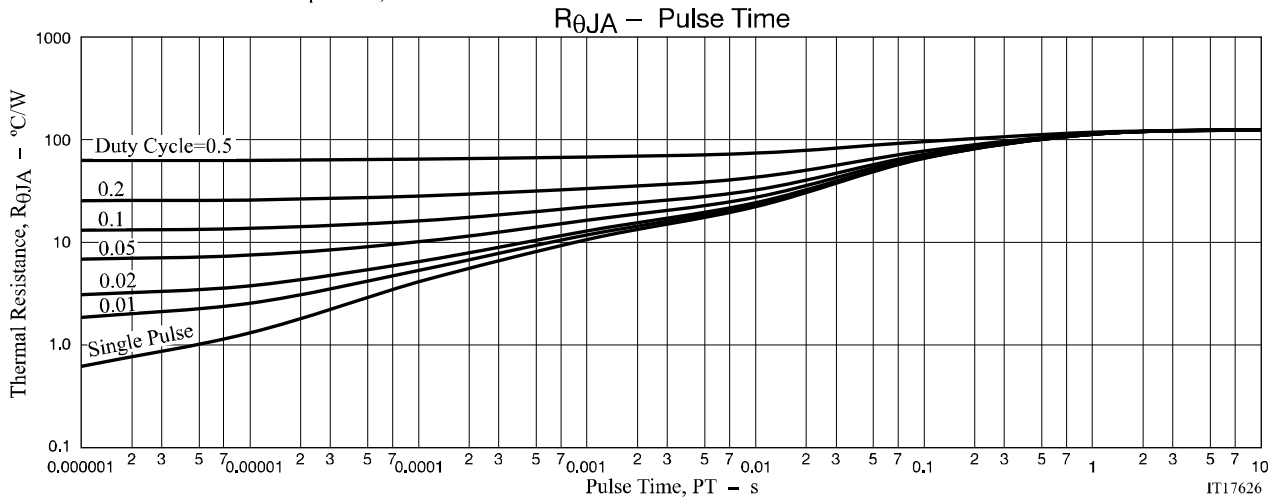
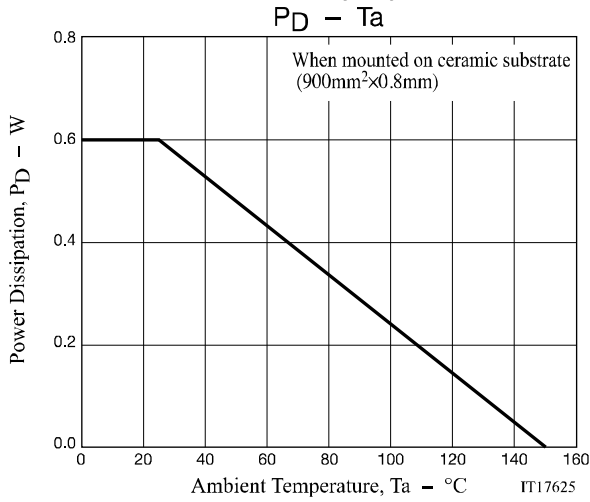
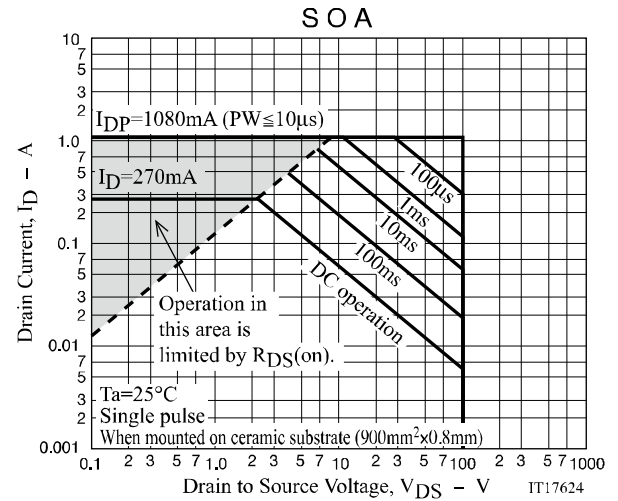
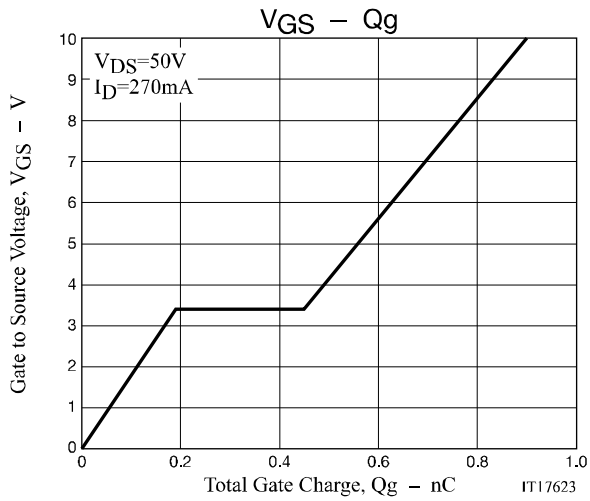


Switching Time Test Circuit





1HN04CH



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[ON Semiconductor:](#)

[1HN04CH-TL-W](#)